

# SANYO Semiconductors DATA SHEET

# LA6571 — 5CH Driver for Mini Disk and Compact Disk

### Overview

The LA6571 is 5-channel driver for mini disk and compact disk applications (BTL-AMP: 5CH).

#### Features

- Power amplifier 5-channel built-in.
- IO max 1A
- Level shift circuit built-in.
- Mute circuit (output ON/OFF) with three built-in channels (2-2-1). (Operates independently for each of MUTE1: CH1 and 2, MUTE2: CH3 and 4, and MUTE3: CH5. Not operating for the regulator (REG))
- Regulator (REG) built-in (external PNP transistor). Voltage setting (typ: 1.5V or more) with an external resistor
- Overheat protection circuit (thermal shutdown) built-in.

# **Specifications**

#### **Maximum Ratings** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	V <sub>CC</sub> max		14	V
Maximum output current	I <sub>O</sub> max	Each output for channel 1 to 5.	1	А
Maximum input voltage	V <sub>IN</sub> B		13	V
MUTE pin voltage	VMUTE		13	V
Allowable loss	Pd max	Independent IC	0.8	W
		Mounted on a specified board*	2	W
Operating temperature	Topr		-30 to +85	°C
Storage temperature	Tstg		-55 to +150	°C

\* Mounted on a specified board: 76.1mm×114.3mm×1.6mm glass epoxy

#### **Recommended Operating Conditions** at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage 1	V <sub>CC</sub> 1		4.5 to V <sub>CC</sub> 2	V
Supply voltage 2	V <sub>CC</sub> 2		6 to 13	V

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Parameter	Symbol	Oracititana	Ratings			l la it
		Conditions	min	typ	max	Unit
[ALL Blocks]						
No-load current drain ON	I <sub>CC</sub> ON	All outputs ON *1		30	50	mA
No-load current drain OFF	I <sub>CC</sub> OFF	All outputs OFF *1		10	20	mA
VREF input voltage range	VREF-IN		1		V <sub>CC</sub> 2-1	V
Thermal shutdown temperature	TSD	*7	150	175	200	°C
[BTL AMP Block] (CH1 to CH5)						
Output offset voltage	VOFF	Voltage difference in output between BTL AMP and each channel.	-50		50	mV
Output offset voltage	V <sub>OFF</sub> 1	Voltage difference in output between BTL AMP and each channel.	-80		80	mV
Output voltage	VO	CH1,CH2 *3	3.2	4.0		V
Output voltage	V <sub>O</sub> 1	CH3,CH4,CH5 *4	9.7	10.5		V
Closed-circuit voltage gain	V <sub>G</sub> 1	Gain between input and output for CH1, CH2, and CH5 *2	4.2	5.0	6.0	times
Closed-circuit voltage gain	V <sub>G</sub> 3	Gain between input and output for CH3 and CH4 *2	8.2	9.0	11.0	times
Slew rate	SR	AMP Independent. Multiply 2 between outputs. *7		0.5		V/µs
MUTE ON voltage	V <sub>MUTE</sub> ON	Each MUTE *6	2			V
MUTE OFF voltage	V <sub>MUTE</sub> OFF	Each MUTE *6			0.5	V
[Input AMP Block]						
Input voltage range	V <sub>IN</sub> op		0		V <sub>CC</sub> 2-1.5	V
Output offset voltage	VOFF op		-10		10	mV
Output current (SINK)	SINK op		2			mA
Output current (SOURCE)	SOURCE op	*5	300	500		μΑ
[Power Supply Block] (PNP transisto	or: 2SB632K)					
Regulator output	Vout	For error Amp, $R_L = 10k\Omega$ at buffer	1.2	1.3	1.4	V
REG-IN SINK current	REG-IN-SINK	Base current to external PNP	5	10		mA
Line regulation	ΔV <sub>O</sub> LN	$6V \le V_{CC} \le 12V$ , $I_O = 200mA$		20	150	mV
Load regulation	ΔV <sub>O</sub> LD	$5\text{mA} \le I_{\Omega} \le 200\text{mA}$		50	200	mV

\*1. Current dissipation that is a sum of  $V_{CC}$ 1 and  $V_{CC}$ 2 at no load.

\*2. Input AMP is a BUFFER AMP.

\*3. Voltage difference between both ends of load (8 $\Omega$ ). Output saturated.

\*4. Voltage difference between both ends of load (12 $\Omega$ ). Output saturated.

\*5. The source of input OP-AMP is a constant current. (See the specified block diagram.)

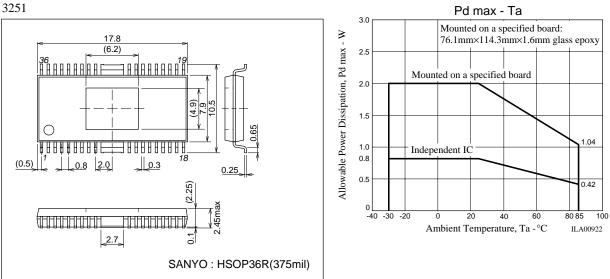
As the  $11k\Omega$  resistance to the next stage is a load, pay due attention when setting the input OP-AMP gain.

\*6. Output ON with MUTE: [H] and OFF with MUTE: [L] (HI impedance).

\*7. Design guarantee value

# Package Dimensions

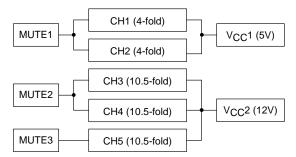
unit : mm



# **Pin Description**

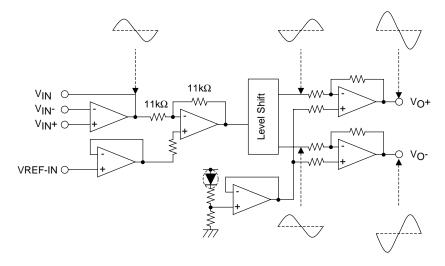
Pin Name	Pin Name	Pin No.	Equivalent Circuit Diagram	Description
Input	VIN <sup>1+</sup>	17		Each input pin
	V <sub>IN</sub> 1 <sup>-</sup>	16	VIN- OVIN O	
	V <sub>IN</sub> 1	15		
	$V_{IN}2^+$	20		
	V <sub>IN</sub> 2 <sup>-</sup>	19		
	V <sub>IN</sub> 2	18		
	V <sub>IN</sub> 3+	23		
	V <sub>IN</sub> 3-	22		
	V <sub>IN</sub> 3	21		
	$V_{IN}4^{-}$	30		
	$V_{IN}4^+$	29		
	V <sub>IN</sub> 4	31		
	$V_{IN}5^+$	32		
	V <sub>IN</sub> 5 <sup>-</sup>	33		
	V <sub>IN</sub> 5	34		
Output	V01+	12	_	Each output
	V <sub>O</sub> 1 <sup></sup>	13		
	V <sub>O</sub> 2 <sup>+</sup>	10		
	V <sub>O</sub> 2-	11		
	V <sub>O</sub> 3+	8		
	V <sub>O</sub> 3-	9	↓ ↓ vo	
	V04+	6		
	V <sub>O</sub> 4-	7		
	V <sub>O</sub> 5 <sup>+</sup>	5		
	V <sub>O</sub> 5-	4		
MUTE	MUTE1	1		Turns ON/OFF the output for
	MUTE2	2		MUTE1: CH1, 2
	MUTE3	36		MUTE2: CH3, 4, and
				MUTE3: CH5.
				Each MUTE operates
				independently.
				MUTE: H output ON
				MUTE: L output OFF
				With the output OFF, the output has a high impedance.
			S-GND ()	output has a high impedance.



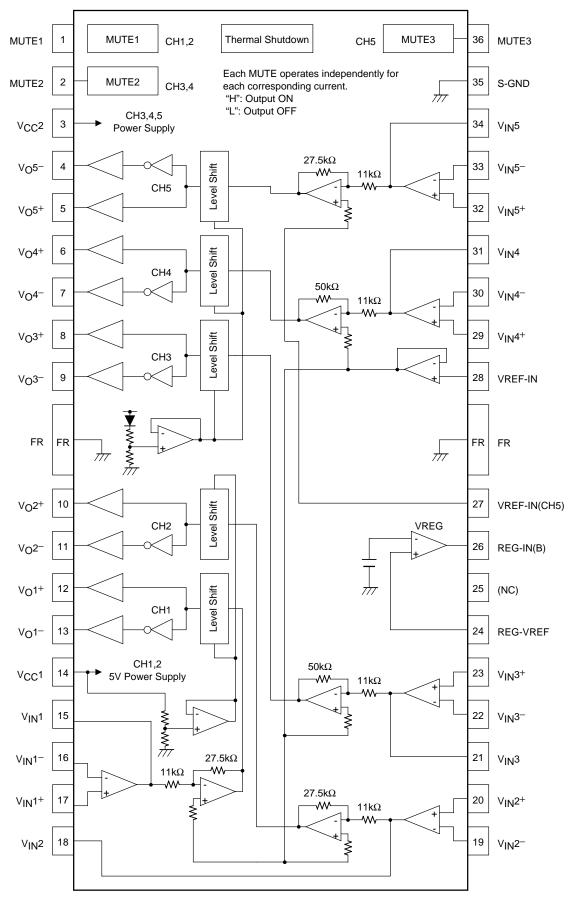


\* MUTE operates independently for each corresponding channel.

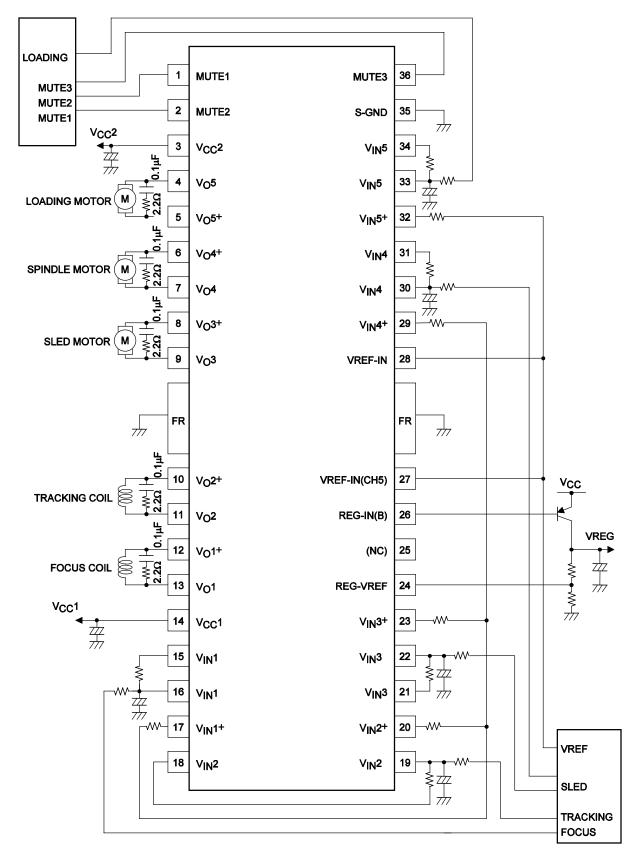
# Schematic Diagram of I/O Related Components







# Sample Application Circuit



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